

Non-Contacting Eddy Current Conductivity Sensor

for Measuring Doped Silicon Wafers

For MEMS Applications

A Finite Element Analysis (FEA) using flexPDE

Craig E. Nelson - Consultant Engineer

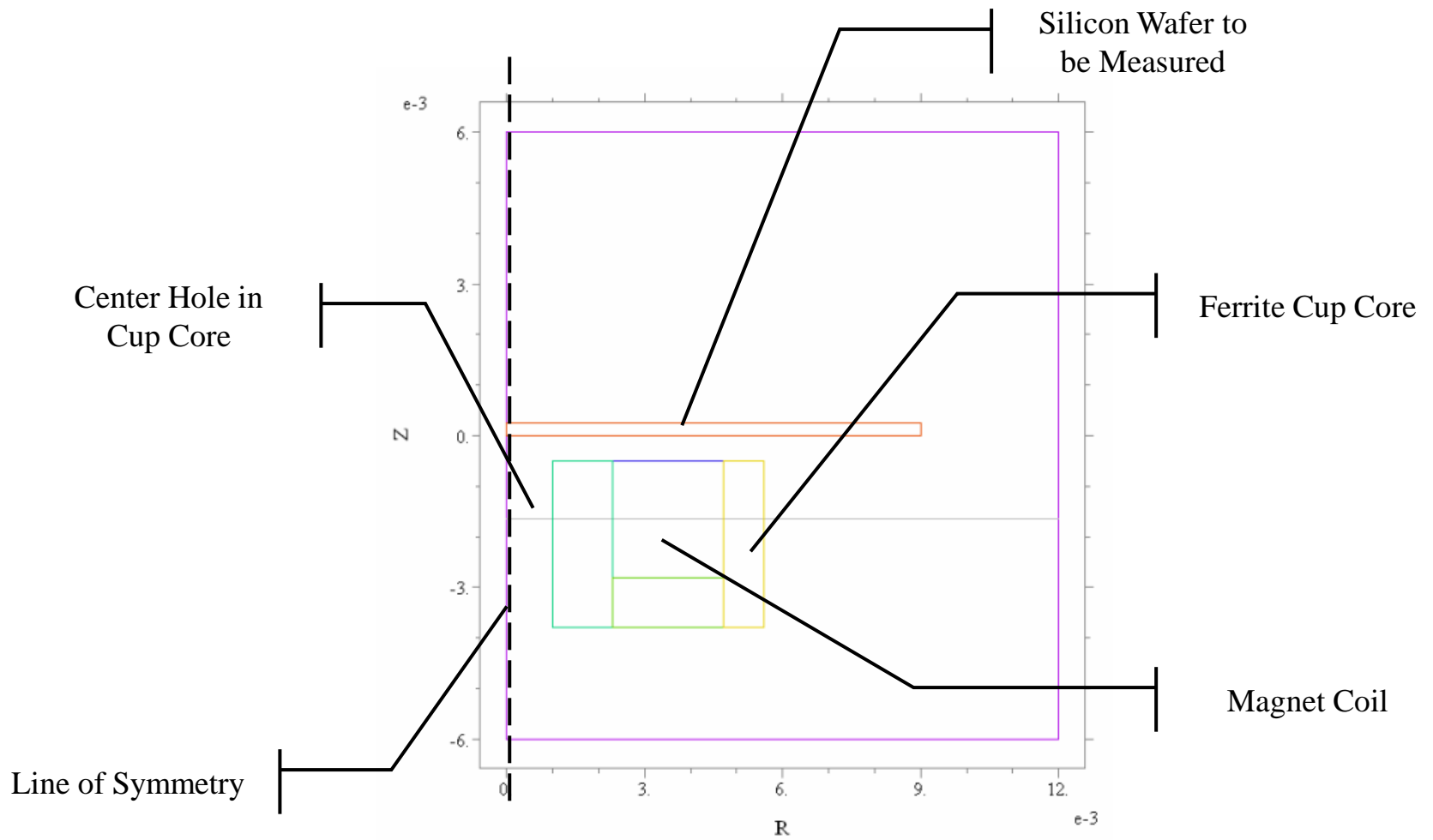
Purpose of the Numerical Experiment:

The purpose of this numerical experiment is to learn something about the electromagnetic fields, induced currents and absorbed power in and around a silicon wafer placed above a “cup core” coil excited at an RF frequency.

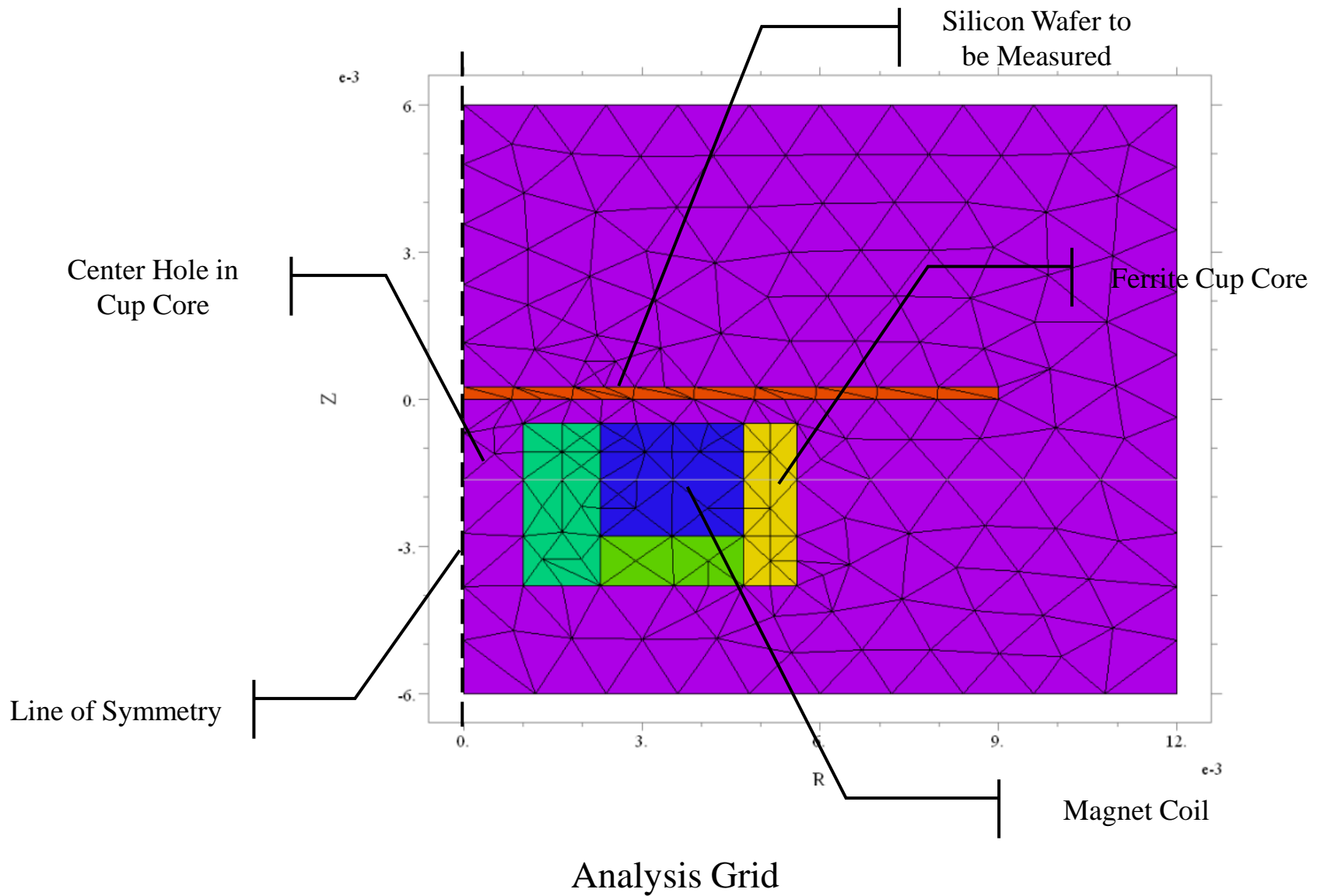
For this analysis, I used an excitation frequency of 5 MHz. However, because I wanted the option of exciting the system at substantially higher frequencies, I employed the full blown Helmholtz wave equation formulation for media that are specified by their permeability, permittivity and conductivity. Because the excitation is sinusoidal, the various field parameters are complex valued.

Using the wave equation approach, the excitation frequency in the model could be raised high enough for radiation of energy from the system to occur ... and ... be accurately evaluated. I was interested in this from a “how much EMI shielding do I need” and “will the shielding lower the performance of the sensor” point of view.

The Model Geometry

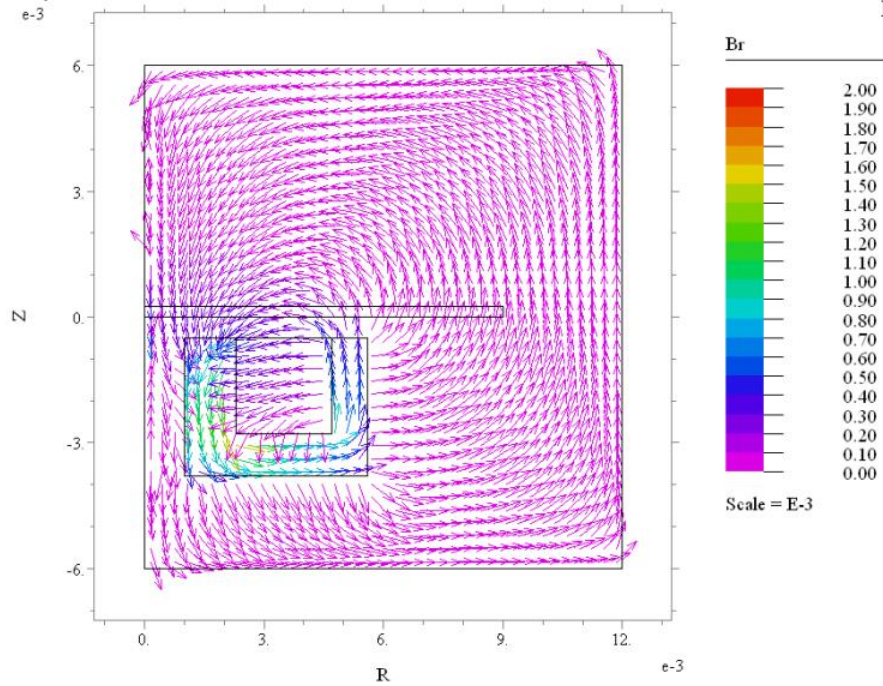


Solution Domain

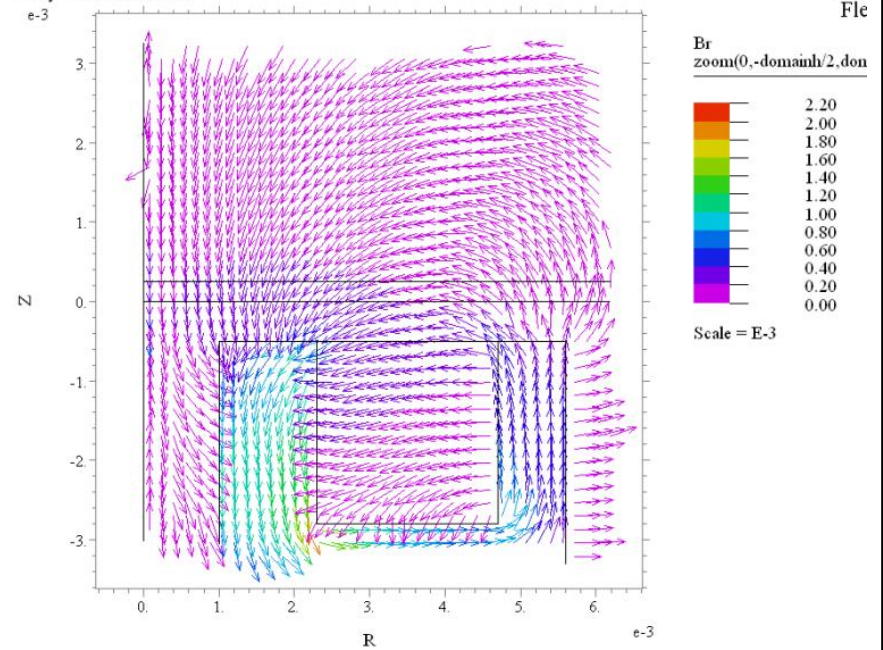


Various Field Plots

Eddy Current Probe

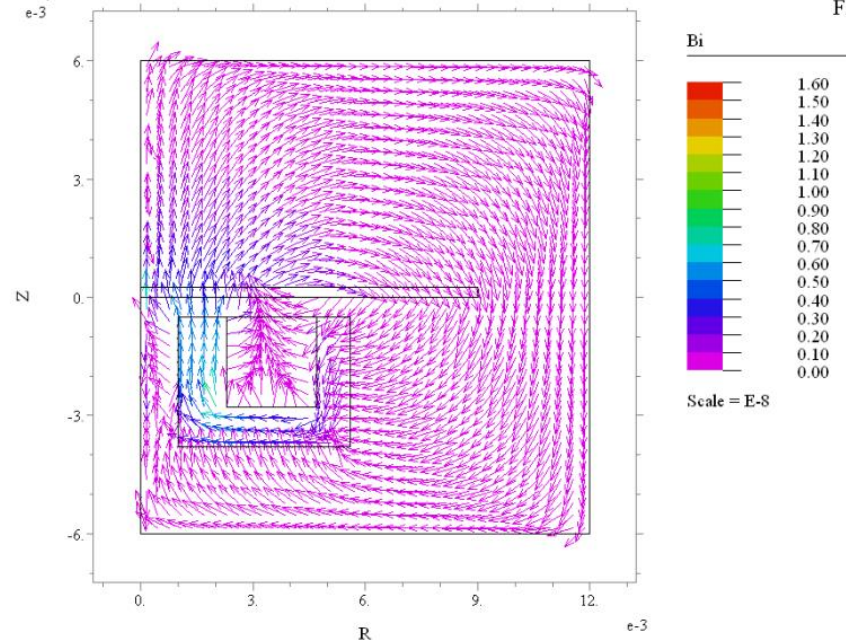


Eddy Current Probe



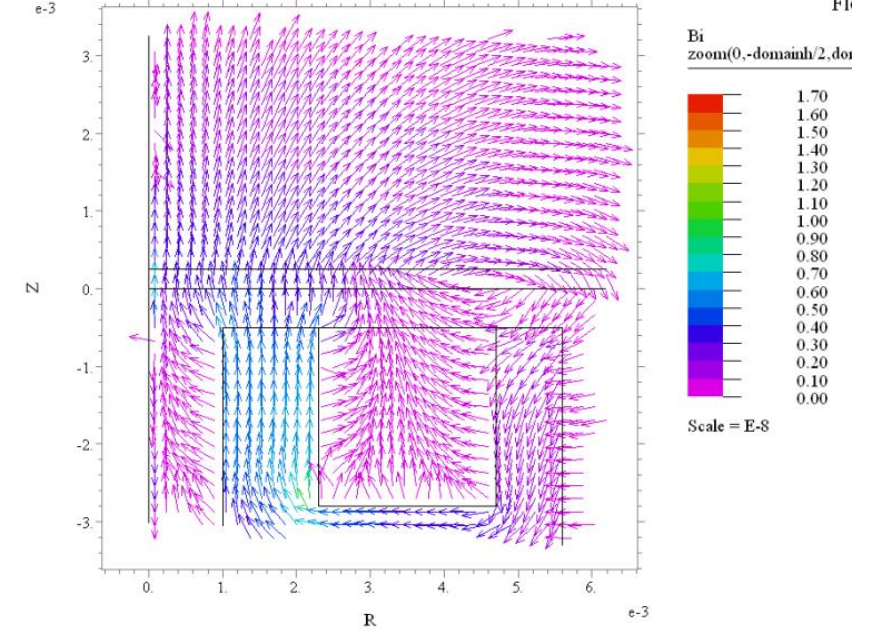
B field – Real Component

Eddy Current Probe



EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058

Eddy Current Probe

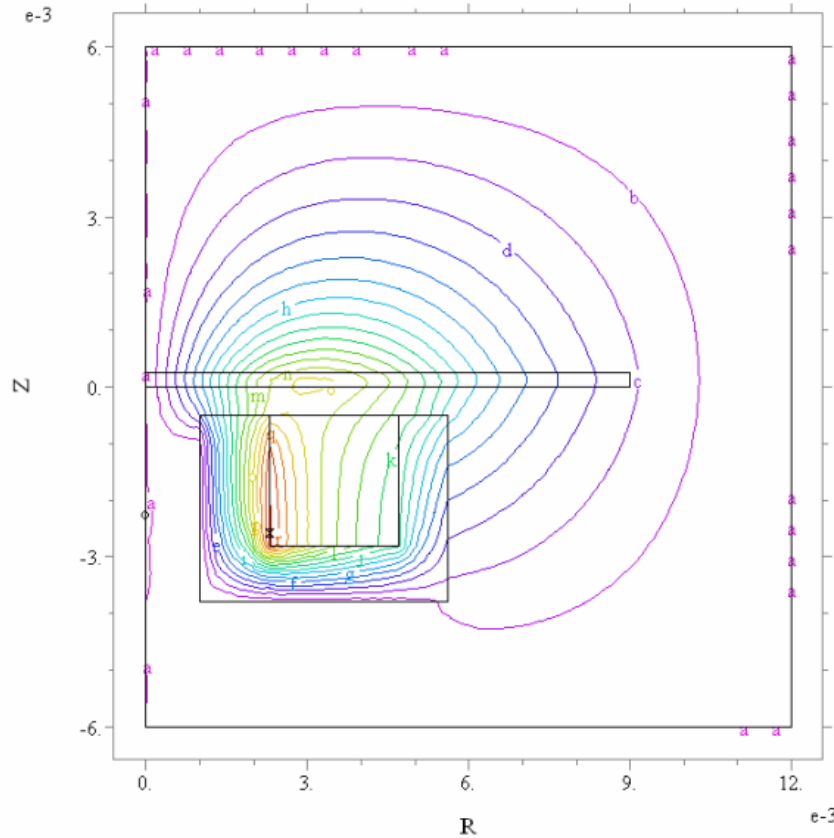


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058

B field – Imaginary Component

Eddy Current Probe

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FlexPDE 5.0.10



Ephi_r

max	1.81
s :	1.80
r :	1.70
q :	1.60
p :	1.50
o :	1.40
n :	1.30
m :	1.20
l :	1.10
k :	1.00
j :	0.90
i :	0.80
h :	0.70
g :	0.60
f :	0.50
e :	0.40
d :	0.30
c :	0.20
b :	0.10
a :	0.00
min	-0.00

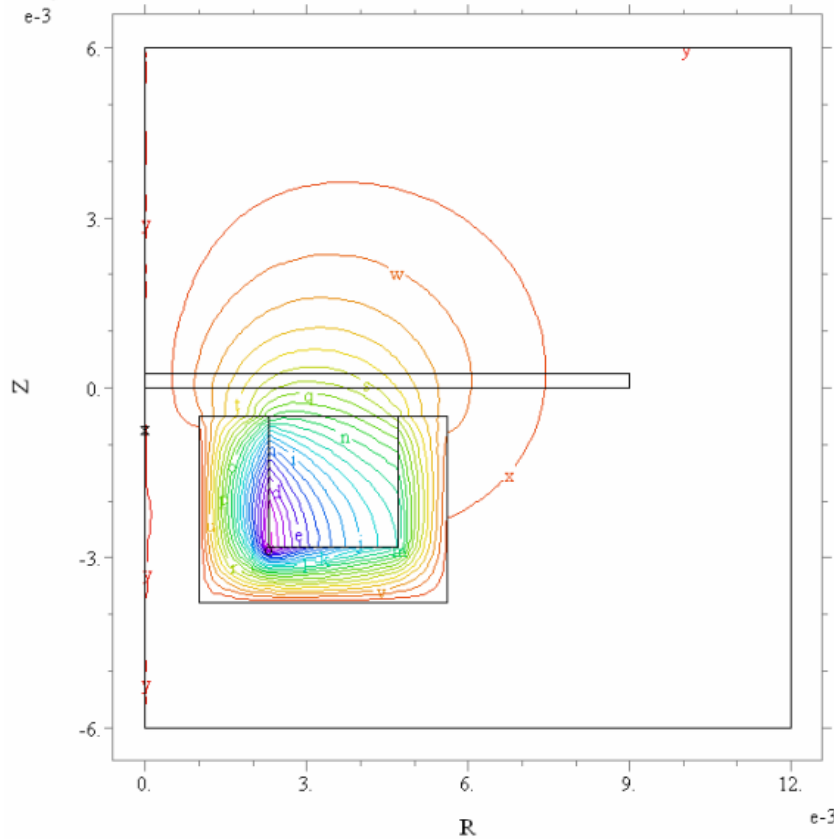
Scale = E-4

EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Vol_Integral= 1.077236e-10

E field – Azimuthal - Real Component

Eddy Current Probe

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Aphir

max	1e-3
y :	0.00
x :	-0.05
w :	-0.10
v :	-0.15
u :	-0.20
t :	-0.25
s :	-0.30
r :	-0.35
q :	-0.40
p :	-0.45
o :	-0.50
n :	-0.55
m :	-0.60
l :	-0.65
k :	-0.70
j :	-0.75
i :	-0.80
h :	-0.85
g :	-0.90
f :	-0.95
e :	-1.00
d :	-1.05
c :	-1.10
b :	-1.15
a :	-1.20
min	-1.23

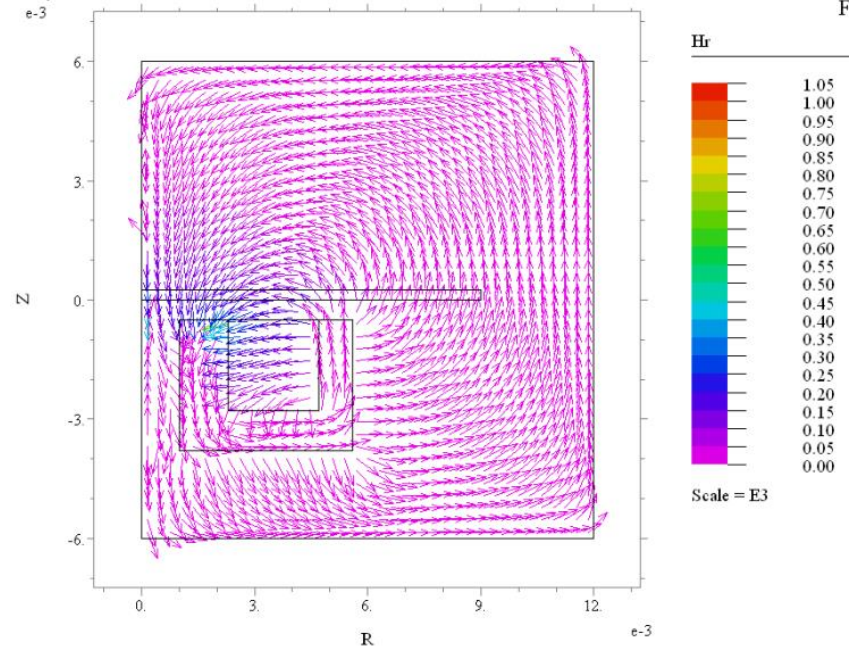
Scale = E-6

EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Vol_Integral= -2.861614e-13

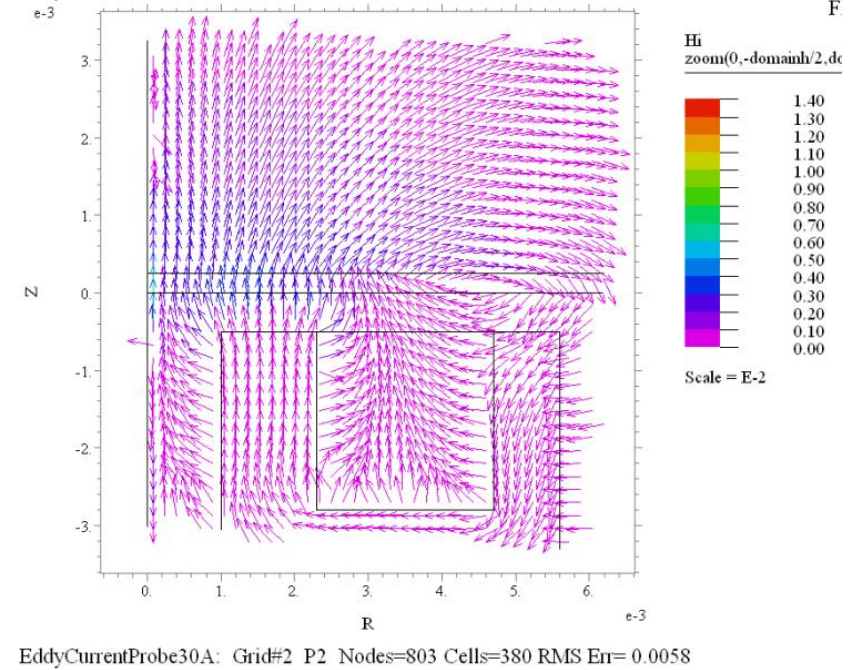
Vector Magnetic Potential field – Azimuthal - Real Component

{ This field effectively shows the magnetic lines of flux }

Eddy Current Probe



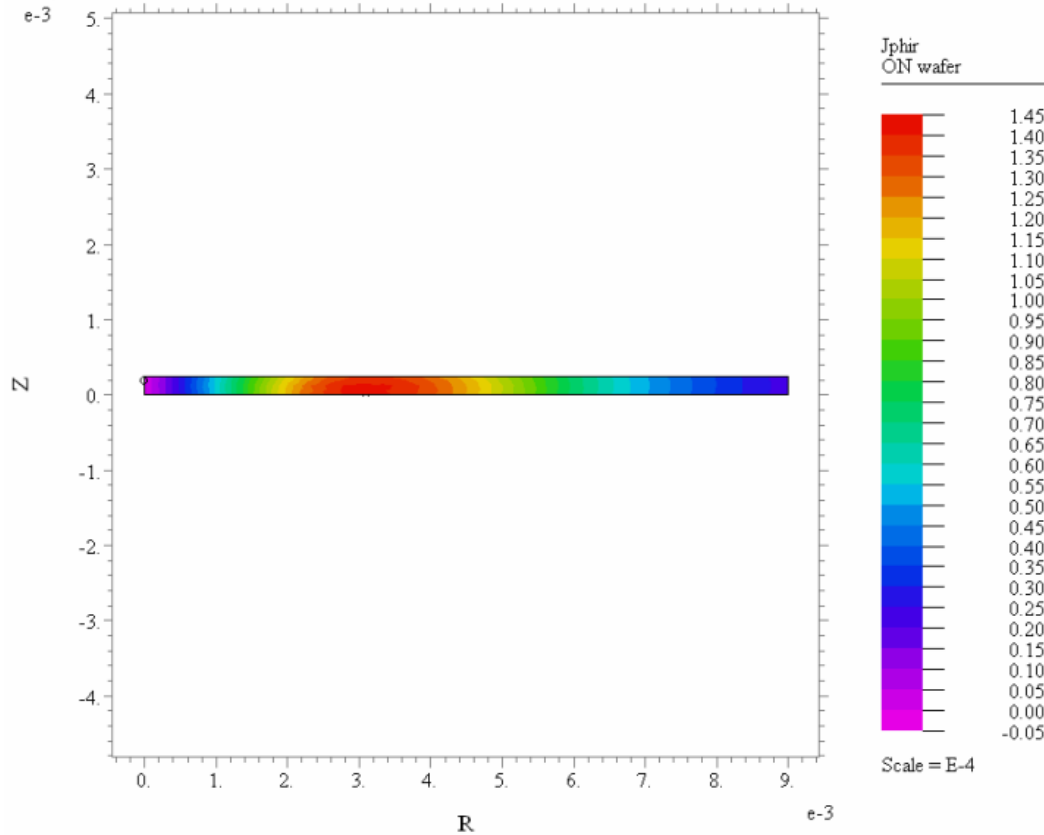
Eddy Current Probe



H Field - Real Component

Eddy Current Probe

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FlexPDE 5.0.10

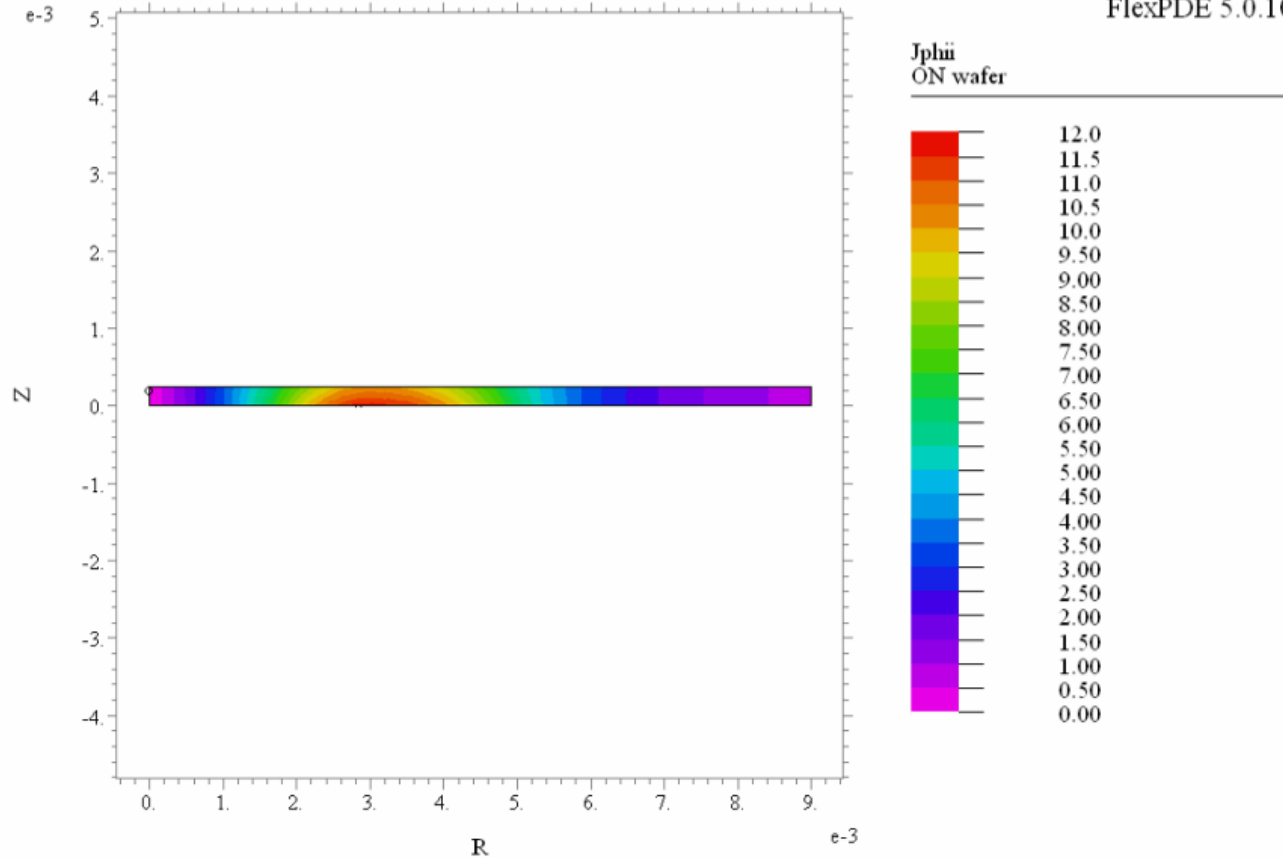


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Vol_Integral= 4.619920e-12

Induced Current Density – Azimuthal - Real Component

Eddy Current Probe

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FlexPDE 5.0.10

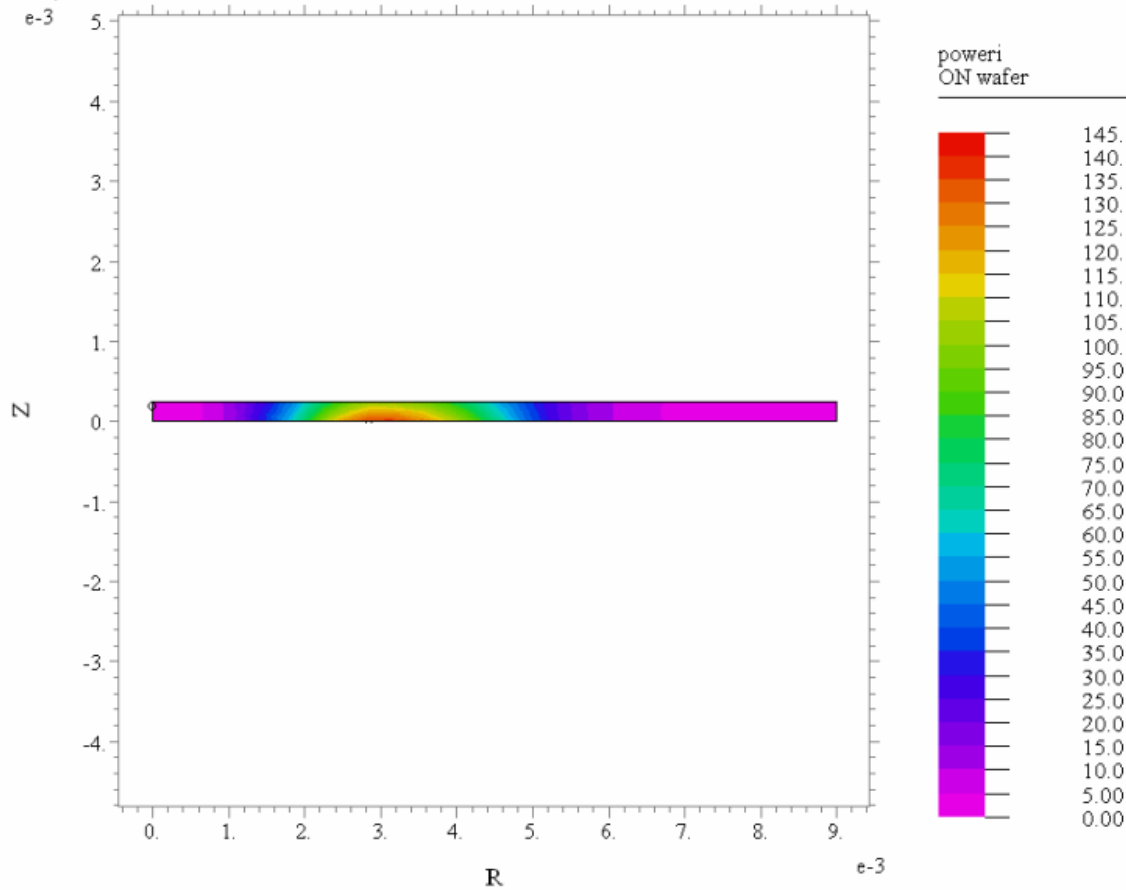


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Vol Integral= 2.652440e-7

Induced Current Density – Azimuthal - Imaginary Component

Eddy Current Probe

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FlexPDE 5.0.10

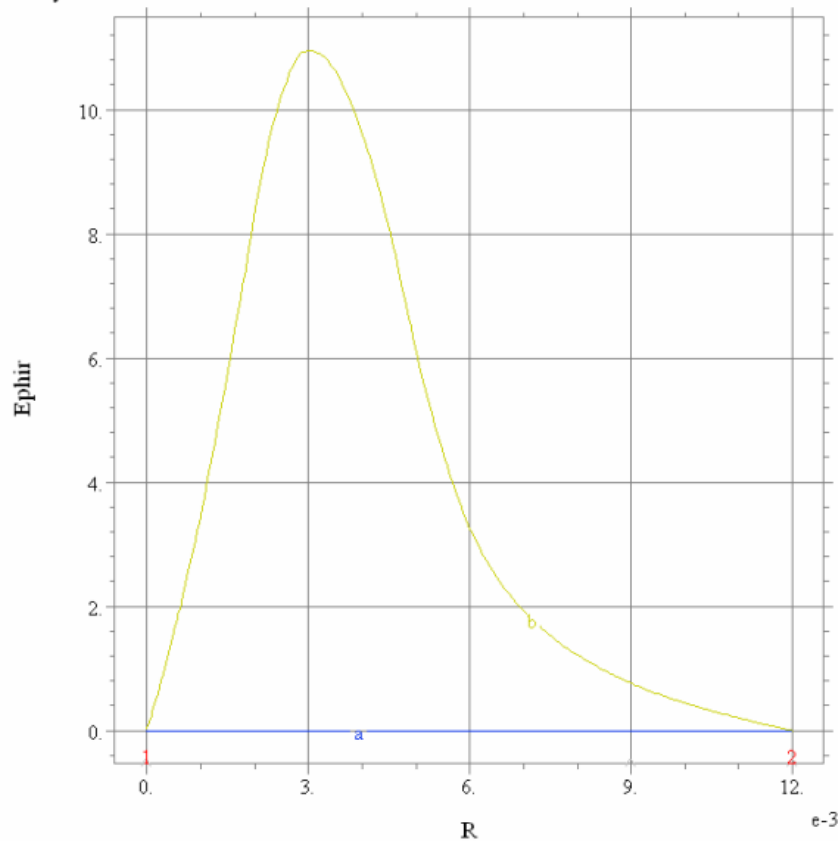


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Vol Integral= 1.855982e-6

Ohmic Power Loss Density

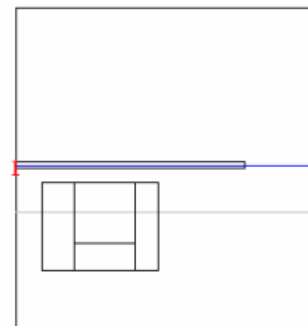
Eddy Current Probe

12:12:13 7/18/07
FlexPDE 5.0.10



Ephi_r
from (0,wafertick/2)
to (domainr,wafertick/2)

a: Ephi_r
b: Ephi_i

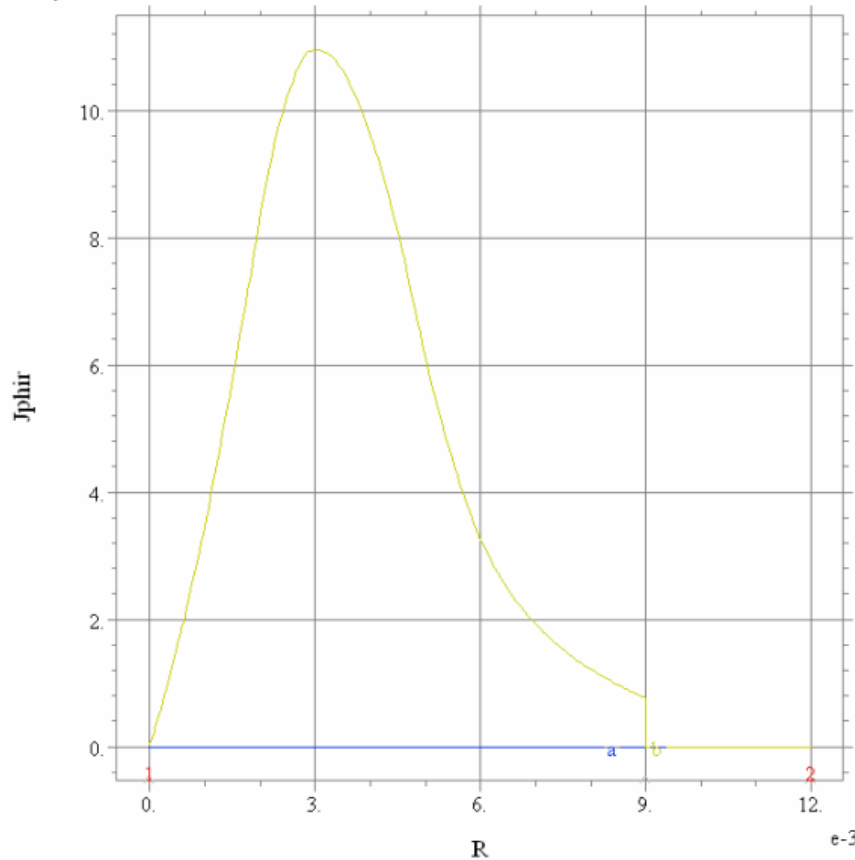


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Surf_Integral(a)= 2.034714e-8 Surf_Integral(b)= 1.123492e-3

E Field on Wafer Center Plane – Azimuthal - Real Component

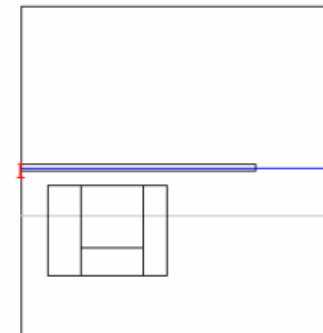
Eddy Current Probe

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FlexPDE 5.0.10



$J_{\phi}(r)$
from (0, waferthick/2)
to (domainr, waferthick/2)

a: $J_{\phi}(r)$
b: $J_{\phi}(r)$

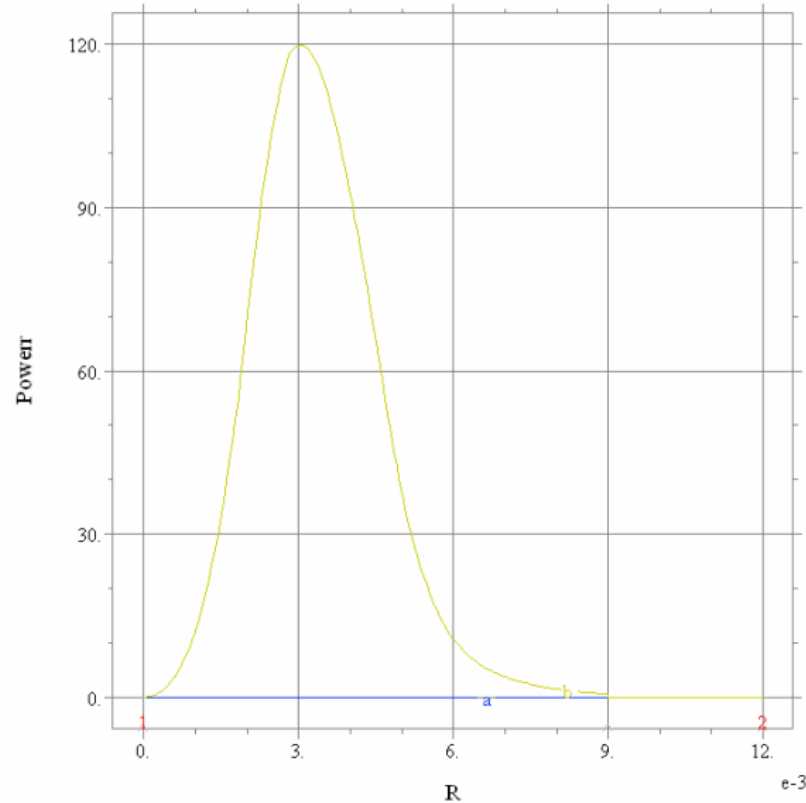


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Surf_Integral(a)= 1.862078e-8 Surf_Integral(b)= 1.060238e-3

Current Density on Wafer Center Plane – Azimuthal - Real Component

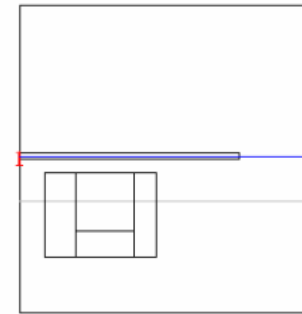
Eddy Current Probe

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FlexPDE 5.0.10



Power
from (0,waferthick/2)
to (domain,waferthick/2)

a: Power
b: Power

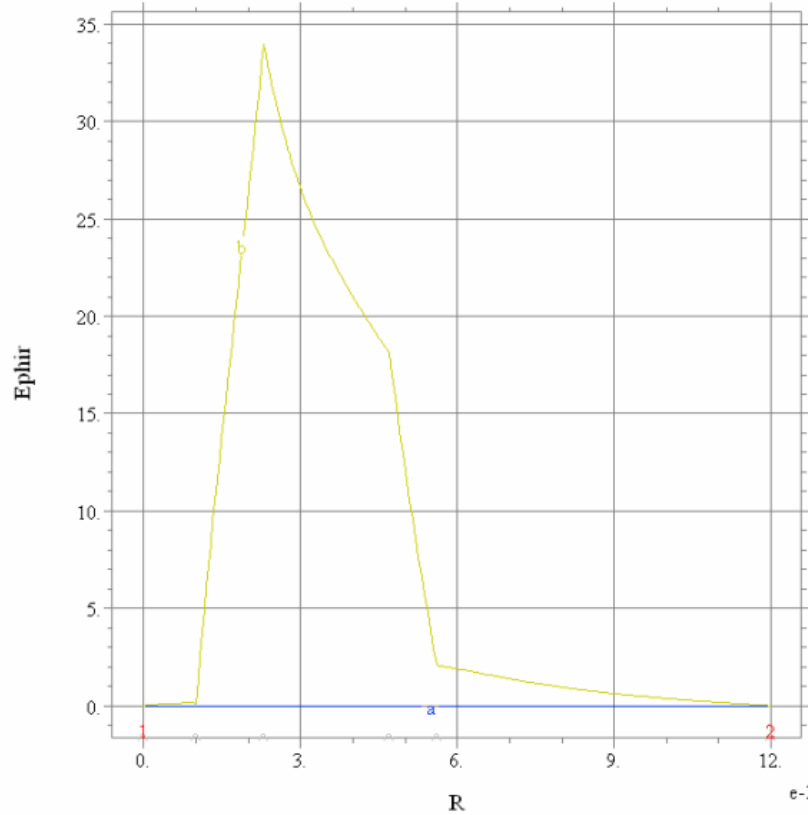


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Surf_Integral(a)= 1.761676e-12 Surf_Integral(b)= 7.386544e-3

Ohmic Power Dissipation on Wafer Center Plane

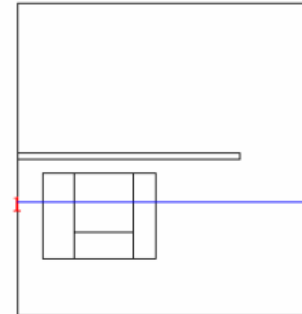
Eddy Current Probe

12:12:13 7/18/07
FlexPDE 5.0.10



Epher
from (0,-gap-(coilheight/2))
to (domain,-gap-(coilheight/2))

a: Epher
b: Ephi

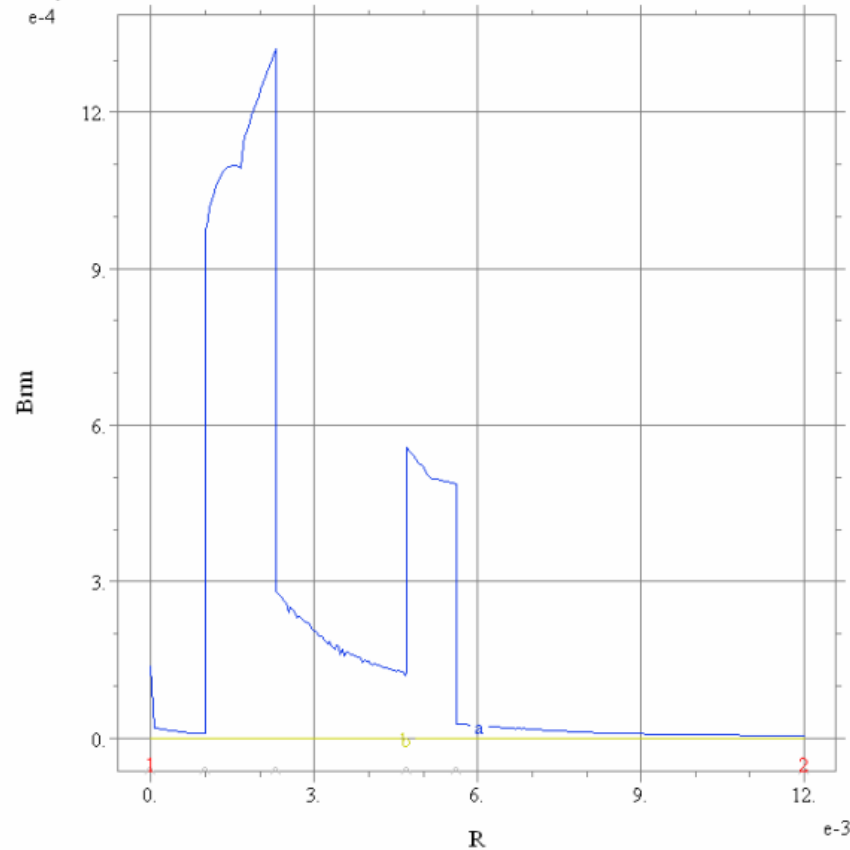


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Surf_Integral(a)= 1.586698e-8 Surf_Integral(b)= 2.020625e-3

E Field on a Cut Plane – Azimuthal - Real Component

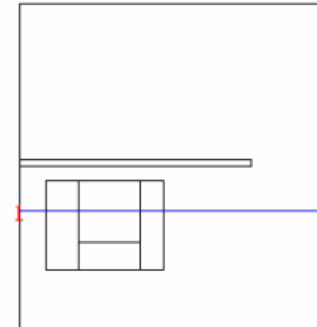
Eddy Current Probe

12:12:13 7/18/07
FlexPDE 5.0.10



Brm
from (0,-gap-(coilheight/2))
to (domain,-gap-(coilheight/2))

a: Brm
b: Bim

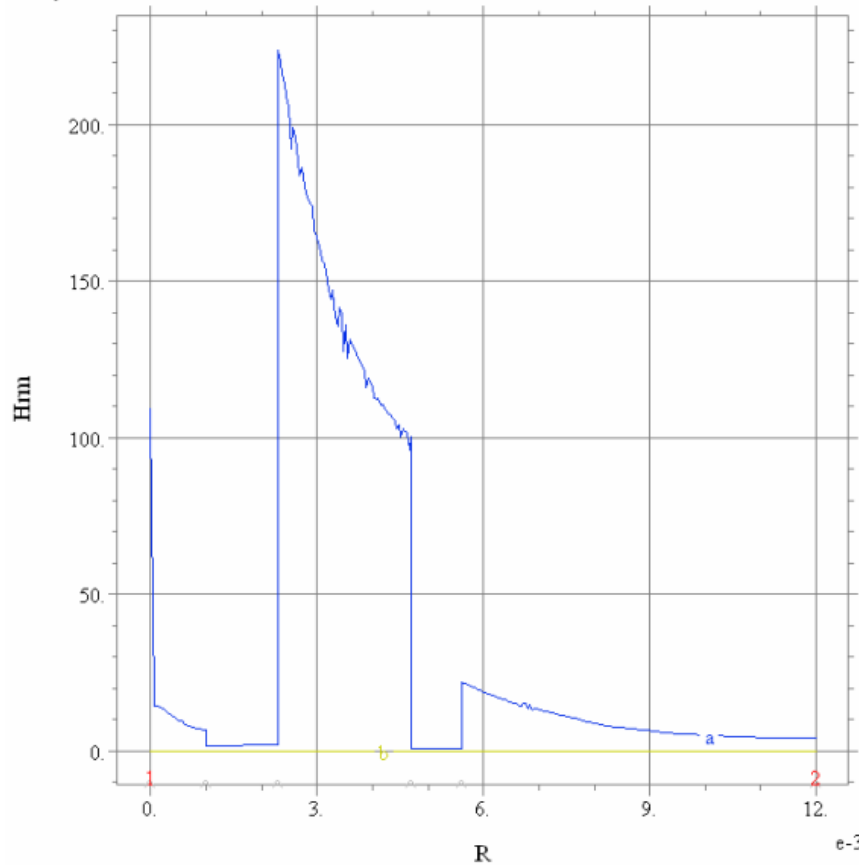


EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Surf_Integral(a)= 4.318249e-8 Surf_Integral(b)= 2.168614e-13

B Field on a Cut Plane – Azimuthal - Real Component

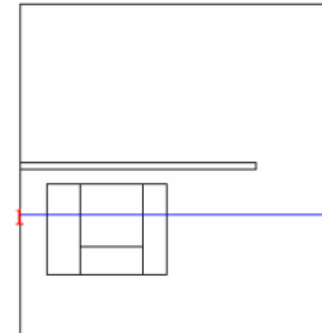
Eddy Current Probe

12:12:13 7/18/07
FlexPDE 5.0.10



H_{rm}
from (0,-gap-(coilheight/2))
to (domainr,-gap-(coilheight/2))

a: H_{rm}
b: H_{im}



EddyCurrentProbe30A: Grid#2 P2 Nodes=803 Cells=380 RMS Err= 0.0058
Surf_Integral(a)= 0.010082 Surf_Integral(b)= 7.649214e-8

H Field on a Cut Plane – Azimuthal - Real Component

Summary of Model Parameters and Resultant Values

Coil Geometry:

coilwidth= 2.400000e-3
coilheight= 2.300000e-3
coilir= 2.300000e-3
coilor= 4.700000e-3
coilwindarea= 8.050000e-6

Material Parameters:

mu0= 1.256637e-6
muferrite= 500.0000
eps0= 8.850000e-12
epsSilicon= 11.70000
sigmacopper= 0.000000
sigmawafer= 1.000000

Coil Current Parameters:

freq= 5000000.
omega= 3.141593e+7
currentcoil= -0.050000
N= 20.00000
Jphicoil= -124223.6

Impedance Parameters:

wafertick= 2.500000e-4
sigmacopper= 0.000000
sigmawafer= 1.000000
Zreal= 4.783306e-15
Zimag= 1.776399e-5
Rcoil= 1.092728e+12
Zcoil= 1.092728e+12
Zcoili= 2.968406
Zintegralr= -1.914173e-15
Zintegrali= 1.051802e-20
Lpoweri= 5.654454e-13
Lpowerr= 1.522573e-22
Zar= 1.641905e-5
Zai= 2.988100
La= 9.511419e-8
Ll1= 9.448730e-8
Lcalc1= 3.647194e-6
Lcalc2= 3.494513e-6

Power Parameters:

sigmacopper= 0.000000
sigmawafer= 1.000000
BfluxIr⁺omega= 2.091582e-4
emflr= 8.144751e-7
emfli= 0.148420
emftotr= 1.628950e-5
emftotf= 2.968406
IRdrop= -5.463639e+10
powercoilr= 0.000000
powercoili= 0.000000
powerwafer= 1.195826e-17
powerwaferi= 4.440998e-8
powertotalr= 1.195826e-17
powertotali= 4.440998e-8

Summary and Conclusions

A finite element model has been developed that allows insight into the nature and magnitude of electromagnetic fields, induced currents and absorbed power in a silicon wafer placed above a “cup core” coil excited at an arbitrary RF frequency.

The model uses the Helmholtz “full wave” formulation which allows analysis of radiation from the system. This model could be developed in many further ways.